# Second Harmonic Generation Induced by Longitudinal Components in Indium Gallium Phosphide Nanowaveguides

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**Abstract:** We experimentally demonstrate second harmonic generation in Indium Gallium Phosphide waveguides by mixing transverse and longitudinal components of the optical fields. We confirm the excitation of an antisymmetric second harmonic mode through modal imaging.

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### 1. Introduction

Integrated photonic circuits are revolutionizing nonlinear optics as they allow for strong confinement in materials with elevated nonlinear indices. While third order nonlinear interaction have been the most studied by far, novel integrated platforms such as lithium niobate [1] or III-V semiconductors on-insulator [2] are renewing interest in second-order nonlinear processes such as second harmonic generation. III-V semiconductors promise record conversion efficiencies as they are characterized by very large second-order nonlinear coefficients (one order of magnitude larger than LiNbO<sub>3</sub>). However, only a single independent tensor element is nonzero ( $\chi^{(2)}_{xyz}$  and permutations). Previous demonstrations of second harmonic generation used waveguides that are rotated by 45° with respect to the crystallographic axes in order to split the main transverse component along two directions [2, 3]. Conversely, we show here that the strong longitudinal component of the pump mode can be leveraged to efficiently generate a second harmonic wave in a waveguide aligned with a crystal axis.

## 2. Theory

We consider a pump optical mode and its second harmonic,  $\vec{E}(\vec{r},t) = \Re\{a(z)\vec{e}_a(x,y)e^{i(\beta_a z - \omega_0 t)} + b(z)\vec{e}_b(x,y)e^{i(\beta_b z - 2\omega_0 t)}\}$ , propagating in a III-V nanowaveguide along the z direction.  $\vec{e}_{a,b}(x,y)$  are the spatial distributions of the electric field in the transverse plane, normalized such that the field amplitudes a, b are expressed in  $\sqrt{W}$ . In the case of negligible propagation loss and pump depletion, the second harmonic power along the waveguide is  $|b(z)|^2 = |\kappa|^2 |a(0)|^4 z^2 \operatorname{sinc}^2(\Delta\beta L/2)$  where  $\Delta\beta = 2\beta_a - \beta_b$  and  $\kappa$  is the effective nonlinearity. When the propagation direction is aligned with a crystallographic axis, it reads:

$$\kappa = \frac{\omega_0 \varepsilon_0}{2} \int \chi_{xyz}^{(2)} \left( e_b^{*x} e_a^y e_a^z + e_b^{*y} e_a^x e_a^z + e_b^{*z} e_a^x e_a^y \right) dA.$$
(1)

Importantly the effective nonlinearity would vanish in this case for purely transverse modes. But in high index contrast waveguides, optical modes are known to display large longitudinal components. We compute the modes of a 680 nm wide, 320 nm thick Indium Gallium Phosphide nanowaveguide. Our simulations predict phase matching between a quasi transverse fundamental pump mode around 1575 nm and a higher order second harmonic mode The effective indices as well as the different electric field component are shown in Fig. 1(a). We readily note the field components of a same mode have very different spatial distributions. Moreover, most have non-negligible amplitudes, confirming the need for full vectorial modeling in order to predict nonlinear coupling in III-V nanowaveguides. We compute an effective nonlinearity  $\kappa = 75(\sqrt{Wm})^{-1}$ , corresponding to a conversion efficiency of  $50\%/(Wcm^2)$ .



Fig. 1. (a) Simulation of the effective indices of a pump mode (black) and a SH mode (green). The spatial distribution of the different electric field components is shown as inset. (b-c) Measured and computed spatial distribution of the intensity of the SH at the output of the waveguide. (d-e) Measured and computed spatial distribution of the intensity of a 775 nm TM fundamental wave for comparison. The field of view for theoretical modes is  $1.5 \ \mu m \ge 1 \ \mu m$ . (f) Second harmonic power collected at the output of the waveguide as a function of the pump wavelength.

### 3. Experimental results

To confirm these theoretical predictions, we fabricated **1.5** mm long InGaP waveguides. We follow the process described in [4] but we rotate the epitaxial stack by  $45^{\circ}$  before bonding it to the silicon-on-insulator wafer. This is because the cleave directions for III-V semiconductors grown on (100) substrate are [110] and [110]. Following the rotation, waveguide facets cleaved along the silicon [011] direction are aligned with a crystallographic axis of the indium Gallium Phosphide layer. We launch a 3 mW telecom band pump in the waveguide through a lensed fiber and collect the second harmonic by use of a high NA (0.9) objective. The sinc<sup>2</sup>-shaped transmission around 775 nm is shown in Fig. 1(c). From the experiment, we estimate a maximum experimental conversion of 0.2 %/W/cm<sup>2</sup> with pump at 1572 nm, in good agreement with the computed phase mathing wavelength. The experimental efficiency however is around 2 orders of magnitude less than the theoretical prediction. This is likely due to strong propagation losses at the second harmonic but could also be because of low collection efficiency or waveguide inhomogeneities. Further experimental investigations are ongoing to shed light on this discrepancy. Next we imaged the second harmonic mode in a microscope arrangement with a nominal magnification of 416. We find good agreement with the theoretical Poynting vector intensity [Fig. 1(c)], confirming the excitation of the predicted antisymetric higher order mode. To calibrate our imaging system, we injected 775 nm light through the lensed fiber to excite a fundamental mode around the SH wavelength [See Fig. 1(d),(e)].

## 4. Conclusion

We experimentally observed second harmonic generation through mixing of transverse and longitudinal field components in an Indium Gallium Phosphide nanowire. Not only does it demonstrate the vector nature of the propagating waves, it also allows to excite higher order modes with different symmetries.

#### References

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